

Product Portfolio



Released

Part Number	Vds (V) min	Rds(on)eff (mΩ) typ	Rds(on)eff (mΩ) max	Id (25°C) (A) max	Package	Package Variation
TP65H035WSQA	650	35	41	47	TO-247	Source
TP65H035WS	650	35	41	46.5	TO-247	Source
TP65H050WS	650	49	60	34	TO-247	Source
TPH3205WSBQA	650	49	62	35	TO-247	Source
TP65H070LDG	650	72	85	25	TO-220	Drain
TP65H070LSG	650	72	85	25	TO-220	Source
TPH3212PS	650	72	85	26	TO-220	Source
TPH3208PS	650	110	130	20	TO-220	Source
TPH3206PSB	650	150	180	16	TO-220	Source
TP90H180PS	900	170	205	15	TO-220	Source



Sampling

Part Number	Vds (V) min	Rds(on)eff (mΩ) typ	Rds(on)eff (mΩ) max	Id (25°C) (A) max	Package	Package Variation
TP65H050BS*	650	50	60	34	TO-263	Source
TP65H150LSG**	650	150	180	15	PQFN88	Source
TP65H300G4LSG***	650	240	290	8	PQFN88	Source
TP90H050WS****	900	50	63	34	TO-247	Source

* Release End of 2019
 ** Release October 2019
 *** Release January 2020
 **** Release Q1 2020

GaN Value Proposition

99% Efficiency
40% Higher Power Density
20% Lower System Cost

Need for Speed
 GaN operates at higher frequencies with up to 4x faster switching, lower crossover losses, and increased system efficiency

Feel the Power
 GaN in a totem-pole configuration lowers component count and EMI filter size to deliver the same power in a smaller footprint

Smaller, Lighter, Cooler
 Higher efficiency and increased power density means lower overall system cost

Transphorm Value Proposition



In production with Tier 1 customers with ramping volumes

- Adoption in high-voltage consumer; computing (Gaming, Crypto-mining, AI); and, infrastructure and IT segments

Best-in-class quality and reliability

- Only JEDEC and AEC-Q101 qualified 650V device(s) available on the market

Comprehensive product portfolio

- 3rd generation of products now in the market and ramping

Manufacturing structure in place to support long-term demand

- Fujitsu foundry relationship for high volume and quality production

Long-term product, package, and automotive roadmap in place